

Growth of Au-doped Mn₄N epitaxial films: substrate dependence

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[Introduction] An antiperovskite ferrimagnetic Mn₄N film is a notable candidate for the domain wall motion devices thanks to its perpendicular magnetic anisotropy^[1] and small spontaneous magnetization ($M_S \sim 100$ kA/m)^[2]. In addition, we can control the properties of Mn₄N by replacing Mn atoms by another element such as Ni^[3].

This time, we focus on Mn_{4-x}Au_xN epitaxial films. Li *et al.* previously reported that the epitaxial growth of Mn_{3.5}Au_{0.5}N film on MgO(001) substrates and the sign reversal of anomalous Hall effect (AHE)^[4]. In this work, we grew Mn_{4-x}Au_xN films on SrTiO₃[STO](001) and MgO(001) and researched their substrate dependences. The lattice mismatches between Mn₄N and these substrates are approximately -0.1% and -6%, respectively.

[Experiment] We fabricated 23-nm-thick Mn_{4-x}Au_xN ($x = 0.4$ and 0.8) films onto STO(001) and MgO(001) substrates by molecular beam epitaxy. Crystalline quality was evaluated by ω -2 θ X-ray diffraction (XRD) and reflection high-energy electron diffraction (RHEED). The Hall effect measurements were conducted at room temperature with a physical properties measurement system (PPMS).

[Result] Figure 1 shows the XRD profiles and RHEED patterns of Mn_{4-x}Au_xN on (a) STO(001) and (b) MgO(001) substrates. Except Mn_{3.2}Au_{0.8}N on STO, we only observed peaks derived from Mn_{4-x}Au_xN and substrates in the XRD profiles, and sharp streaks were observed in the RHEED patterns. The peak shift in XRD indicates that the lattice constant of Mn_{4-x}Au_xN increased by Au doping. The crystalline orientation of Mn_{3.2}Au_{0.8}N on STO is degraded compared to that of Mn_{3.6}Au_{0.4}N due to the lattice mismatch between Mn_{3.2}Au_{0.8}N and the substrate.

Figure 2 shows the anomalous Hall resistivity ρ_{AHE} of Mn_{4-x}Au_xN on MgO(001). We observed the sign reversal of AHE resistivity at $x = 0.4$ and 0.8 . The results of X-ray circular magnetic dichroism will be discussed in talk to show the cause of this sign reversal.

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[Reference]

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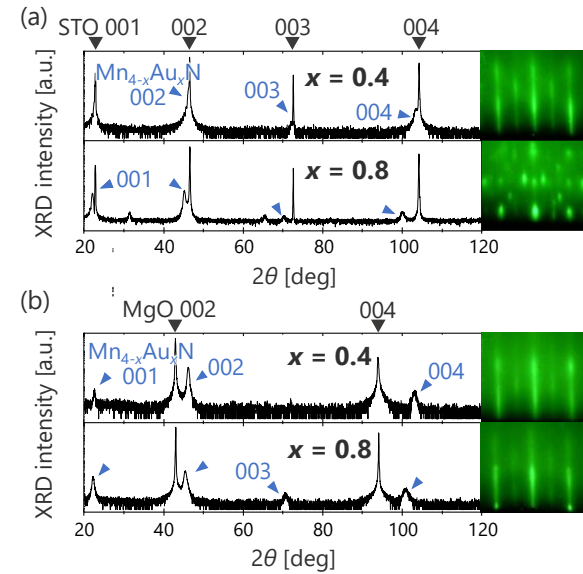


Fig. 2 ω -2 θ XRD profiles and RHEED patterns along [100] azimuth of Mn_{4-x}Au_xN on (a) STO(001) and (b) MgO(001)

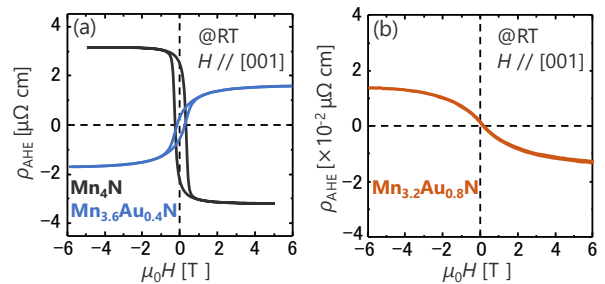


Fig. 1 ρ_{AHE} of (a) Mn₄N, Mn_{3.6}Au_{0.4}N and (b) Mn_{3.2}Au_{0.8}N on MgO(001)